

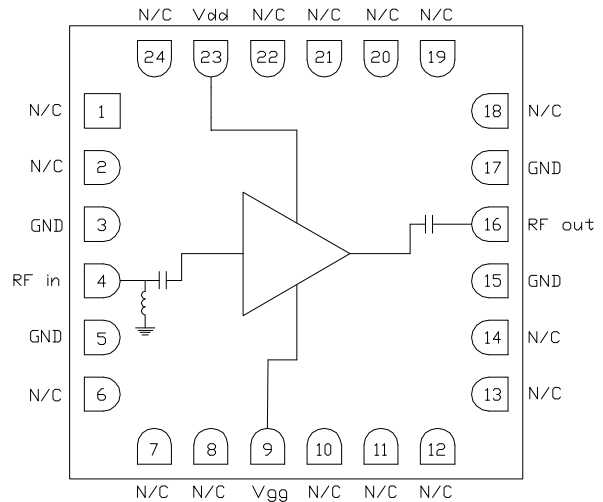
### Features

- ▶ Wide bandwidth
- ▶ Low phase noise
- ▶ Low current consumption
- ▶ Pb-free RoHs compliant 4x4 mm SMT package

### Description

The CMD245C4 is a wideband GaAs MMIC low phase noise amplifier housed in a leadless surface mount package that is ideally suited for military, space and communications systems. At 10 GHz the device delivers 18 dB of gain, a saturated output power of +21 dBm and a noise figure of 4.5 dB. Also with an input signal of 10 GHz the amplifier provides low phase noise performance of -165 dBc/Hz at 10 kHz offset. The CMD245C4 is a 50 ohm matched design which eliminates the need for RF port matching.

### Functional Block Diagram



### Electrical Performance – $V_{dd} = 5.0\text{ V}$ , $V_{gg} = 3.0\text{ V}$ , $T_A = 25\text{ }^\circ\text{C}$ , $F = 10\text{ GHz}$

Parameter	Min	Typ	Max	Units
Frequency Range	5 – 20			GHz
Gain		18		dB
Input Return Loss		10		dB
Output Return Loss		12		dB
Noise Figure		4.5		dB
Output P1dB		18		dBm
Saturated Output Power		21		dBm
Phase Noise @ 10 kHz Offset		-165		dBc/Hz
Supply Current		76		mA

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# CMD245C4

## 6-18 GHz Low Phase Noise Amplifier

### Specifications

#### Absolute Maximum Ratings

Parameter	Rating
Drain Voltage, V <sub>dd</sub>	8.0 V
Gate Voltage, V <sub>gg</sub>	5.0 V
RF Input Power	+17 dBm
Channel Temperature, T <sub>ch</sub>	150 °C
Power Dissipation, P <sub>diss</sub>	602 mW
Thermal Resistance	108 °C/W
Operating Temperature	-40 to 85 °C
Storage Temperature	-55 to 150 °C

Operation of this device outside the maximum ratings may cause permanent damage.

#### Recommended Operating Conditions

Parameter	Min	Typ	Max	Units
V <sub>dd</sub>	3.0	5.0	7.0	V
I <sub>dd</sub>		76		mA
V <sub>gg</sub>	0	3.0	4.0	V

Electrical performance is measured at specific test conditions. Electrical specifications are not guaranteed over all recommended operating conditions.

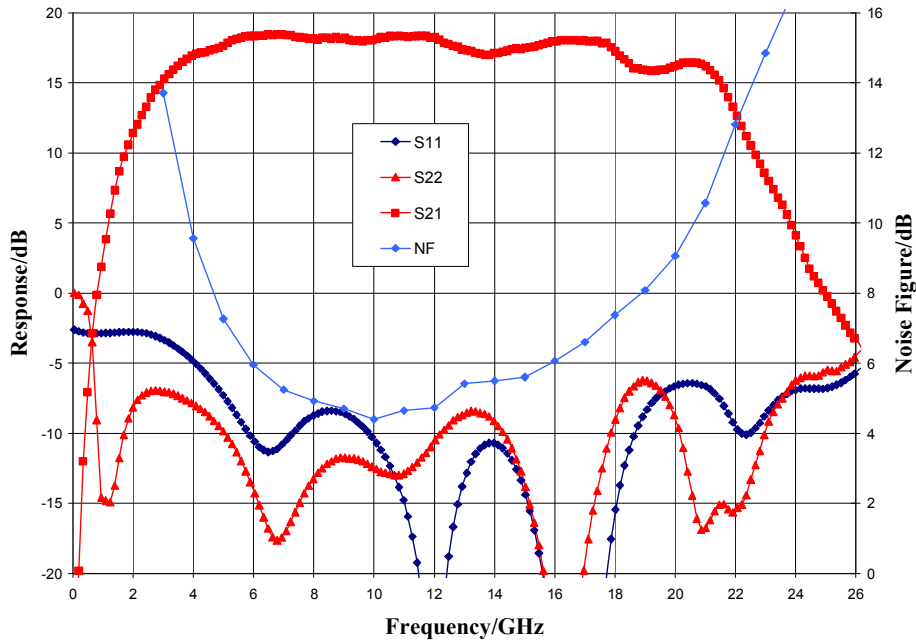
#### Electrical Specifications – V<sub>dd</sub> = 5.0 V, V<sub>gg</sub> = 3.0 V, T<sub>A</sub> = 25 °C

Parameter	Min	Typ	Max	Min	Typ	Max	Units
Frequency Range	6 – 12			12 – 18			GHz
Gain	15	18	21.5	14	17.5	21.5	dB
Noise Figure		5			6		dB
Input Return Loss		10			15		dB
Output Return Loss		13			12		dB
Output P1dB	15	19		11	16		dBm
Saturated Output Power		21			20		dBm
Output IP3		29			29		dBm
Phase Noise @ 10 kHz Offset		-165			-165		dBc/Hz
Supply Current	53	76	100	53	76	100	mA

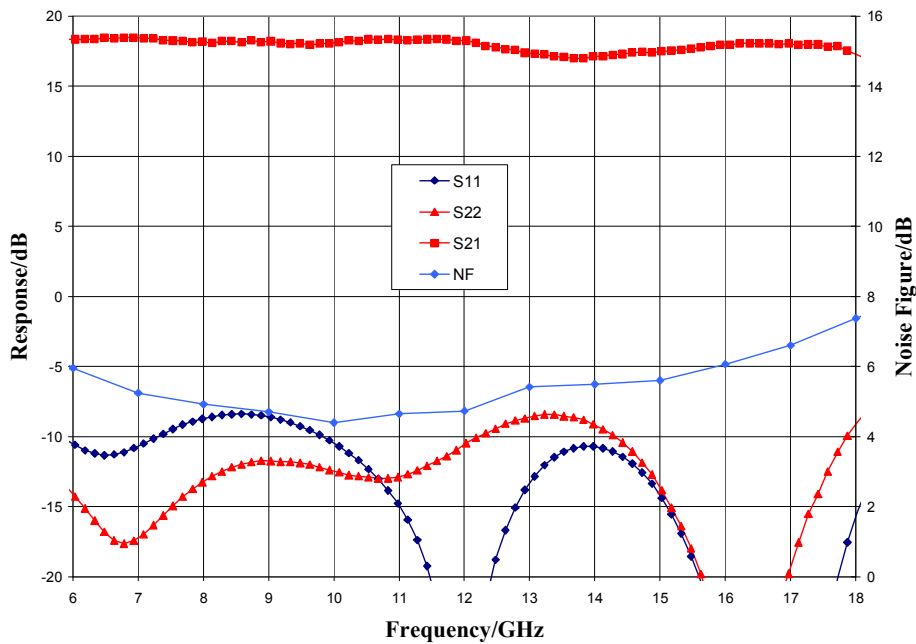
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### Typical Performance

**Broadband Performance,  $V_{dd} = 5.0\text{ V}$ ,  $V_{gg} = 3.0\text{ V}$ ,  $I_{dd} = 76\text{ mA}$ ,  $T_A = 25\text{ }^\circ\text{C}$**



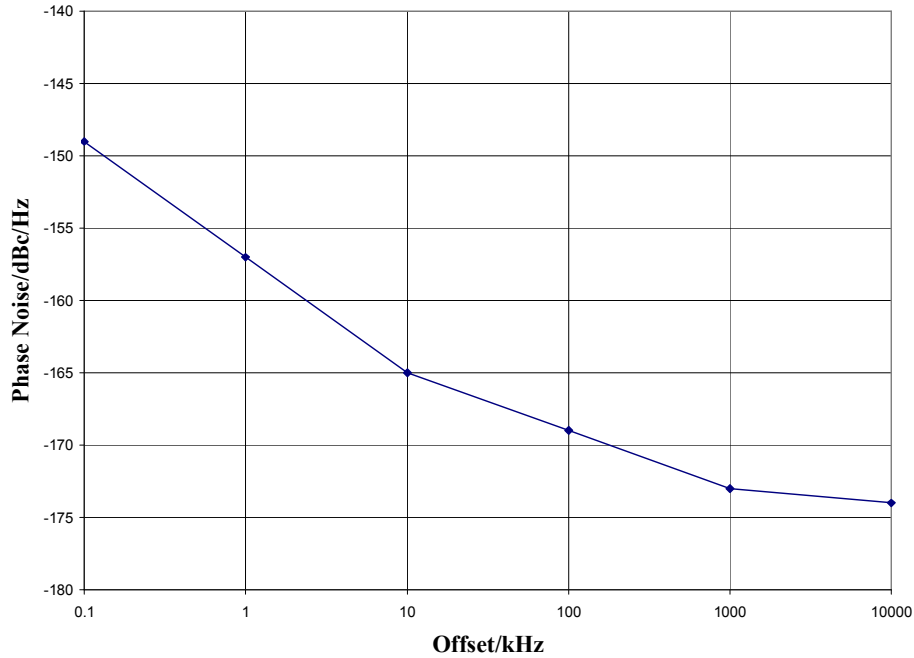
**Narrow-band Performance,  $V_{dd} = 5.0\text{ V}$ ,  $V_{gg} = 3.0\text{ V}$ ,  $I_{dd} = 76\text{ mA}$ ,  $T_A = 25\text{ }^\circ\text{C}$**



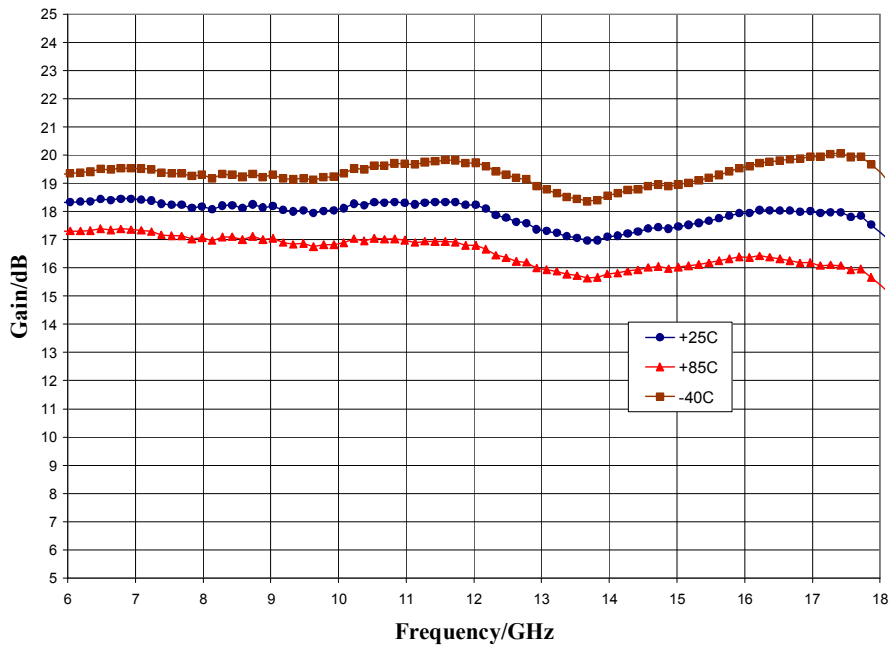
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### Typical Performance

Additive Phase Noise @ P<sub>sat</sub>, V<sub>dd</sub> = 5.0 V, V<sub>gg</sub> = 3.0 V, T<sub>A</sub> = 25 °C



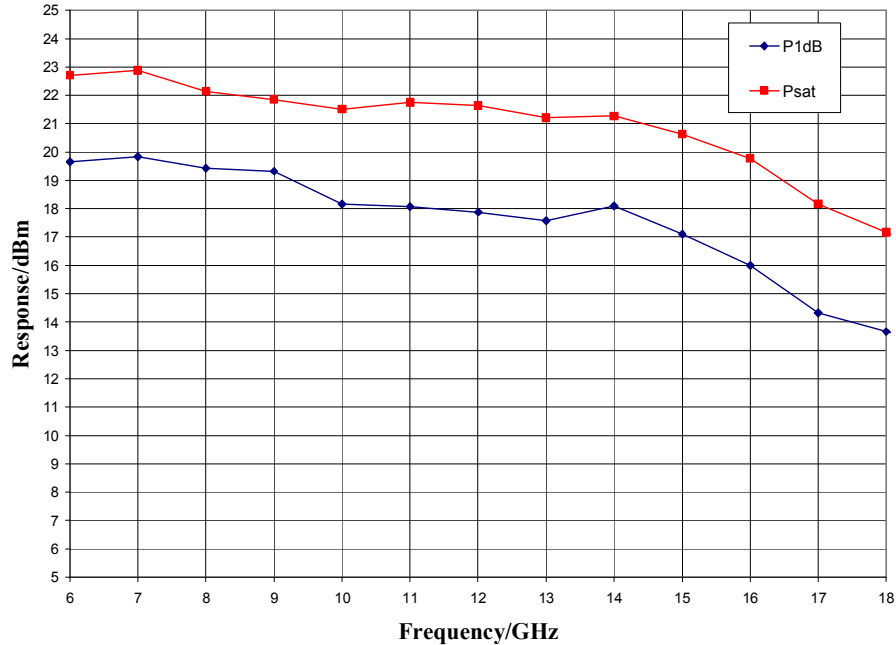
Gain vs. Temperature, V<sub>dd</sub> = 5.0 V, V<sub>gg</sub> = 3.0 V



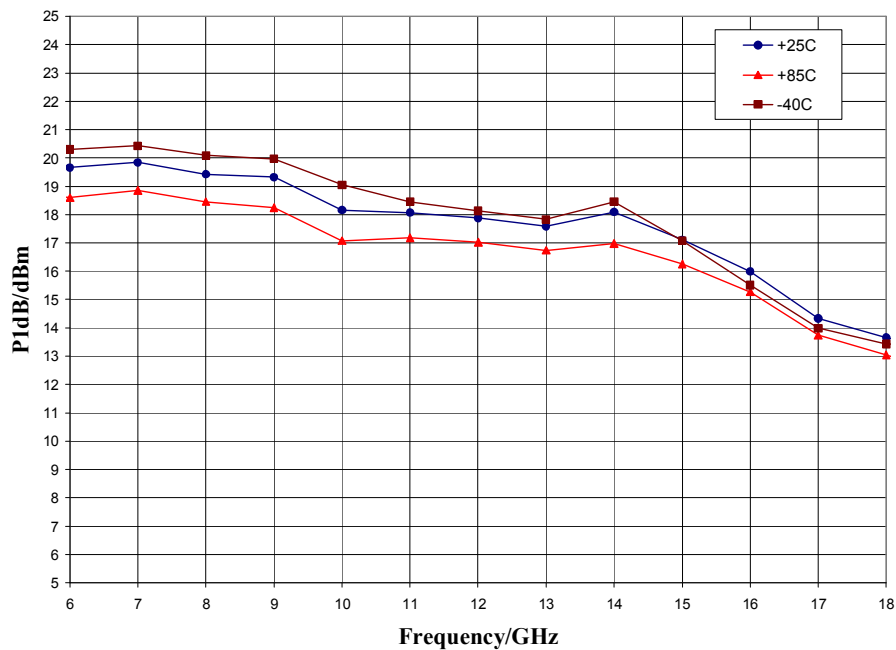
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### Typical Performance

Output Power,  $V_{dd} = 5.0\text{ V}$ ,  $V_{gg} = 3.0\text{ V}$ ,  $T_A = 25\text{ }^\circ\text{C}$

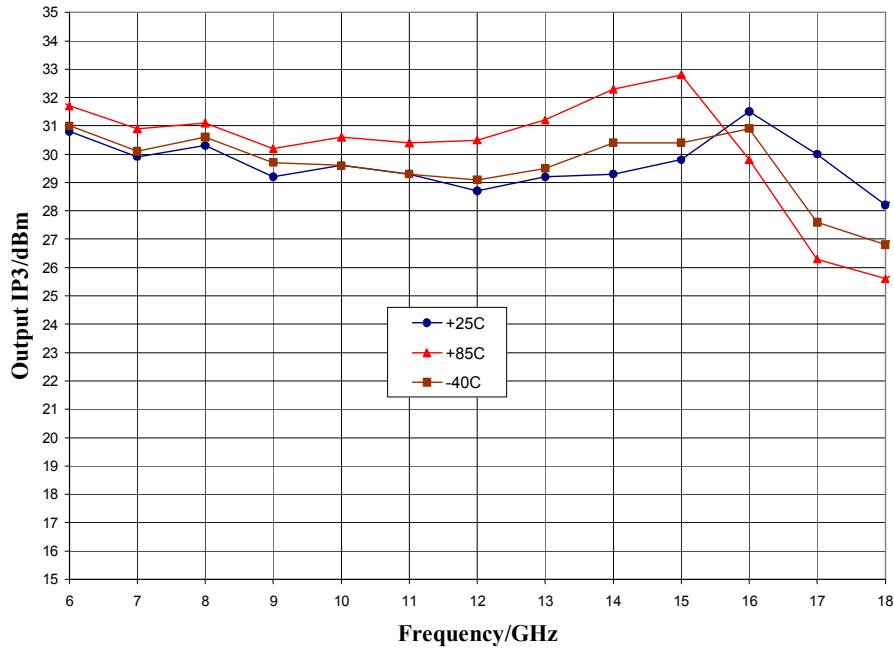


P1dB vs. Temperature,  $V_{dd} = 5.0\text{ V}$ ,  $V_{gg} = 3.0\text{ V}$

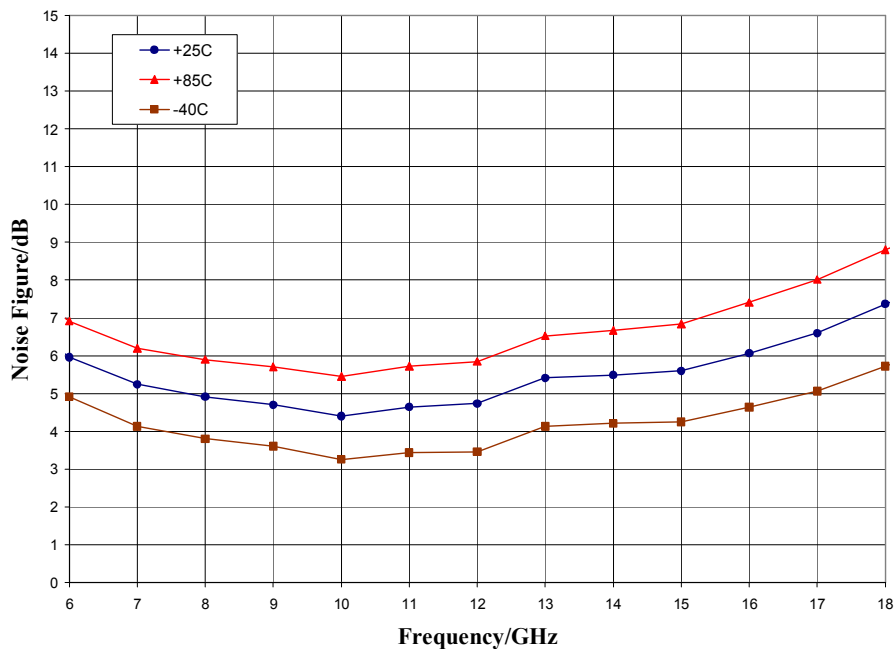


### Typical Performance

**Output IP3 vs. Temperature,  $V_{dd} = 5.0\text{ V}$ ,  $V_{gg} = 3.0\text{ V}$**

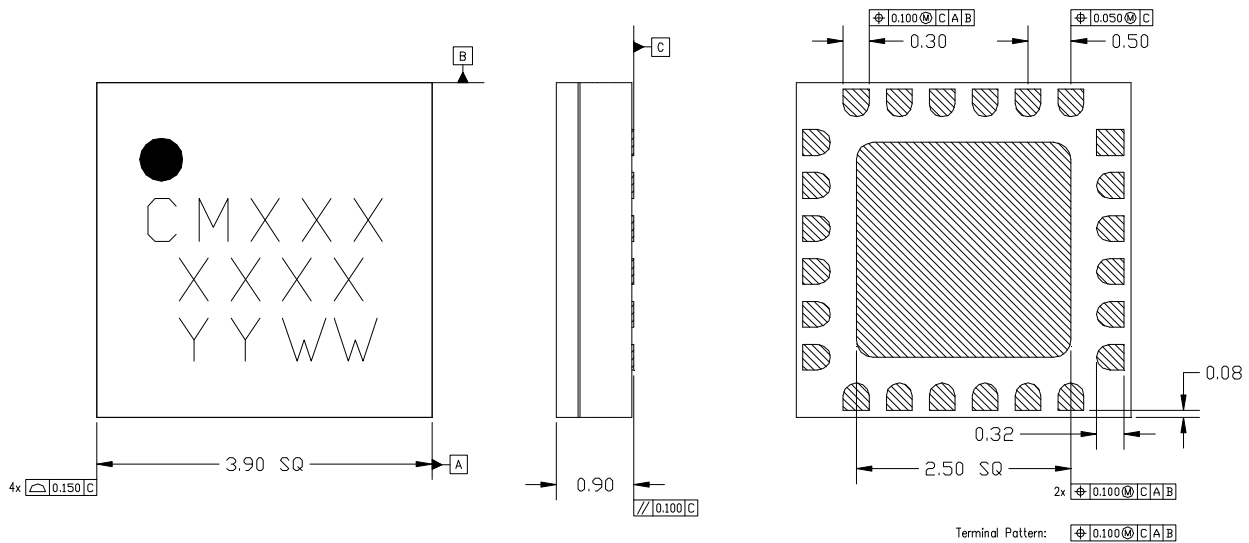


**Noise Figure vs. Temperature,  $V_{dd} = 5.0\text{ V}$ ,  $V_{gg} = 3.0\text{ V}$**



### Mechanical Information

#### Package Information and Dimensions



- NOTES:
1. ALL DIMENSIONS SHOWN IN mm.
  2. MATERIAL: BLACK ALUMINA
  3. LEAD FINISH:
    - 3.1. Ni: 8.89um MAX, 1.27um MIN
    - 3.2. Pd: 0.17um MAX, 0.07um MIN
    - 3.3. Au: 0.254um MAX, 0.03um MIN
  4. MARKING
    - 4.1. LINE 1: PART NUMBER
      - 4.1.1. EXAMPLE: CMD191C4 SHALL BE MARKED AS CM191
    - 4.2. LINE 2: LOT NUMBER
    - 4.3. LINE 3: DATE CODE - LAST 2 DIGITS OF THE YEAR OF MANUFACTURE FOLLOWED BY A 2 DIGIT WEEK CODE
  5. ALTERNATE PIN #1 IDENTIFIER IS A SINGLE SQUARE PAD
  6. ALTERNATE DIE PADDLE MAY HAVE CHAMFERED CORNERS

#### Recommended PCB Land Pattern

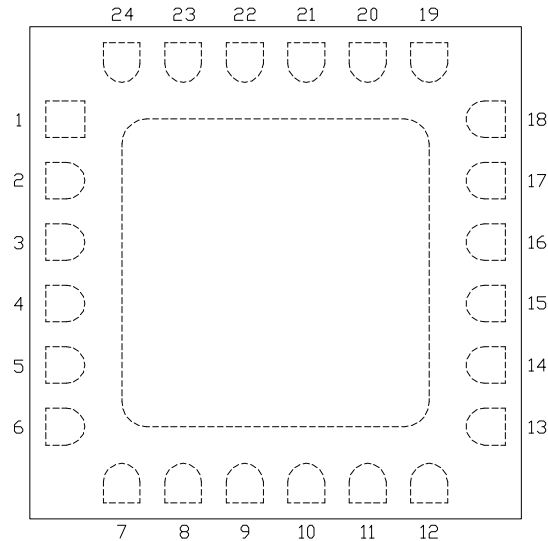
Custom MMIC Design Services recommends that the user develop the land pattern that will provide the best design for proper solder reflow and device attach for their specific application. Please review Custom MMIC Application Note AN 105 for a recommended land pattern approach.

#### Recommended Solder Reflow Profile


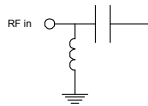
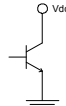

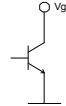
Custom MMIC Design Services recommends screen printing with belt furnace reflow to ensure proper solder reflow and device attach. Please review Custom MMIC Application Note AN 102 for a recommended solder reflow profile.

### Pin Description

#### Pin Diagram



#### Functional Description

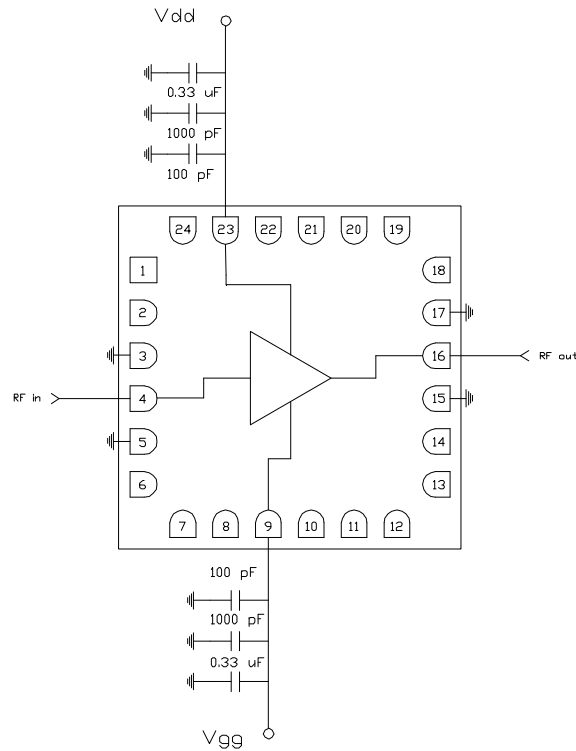
Pad	Function	Description	Schematic
1, 2, 6-8, 10-14, 18-22, 24	N/C	No connection required. These pins may be connected to RF/DC ground.	
3, 5, 15, 17 and die paddle	Ground	Connect to RF / DC ground	
4	RF in	DC coupled and 50 ohm matched	
23	Vdd	Power supply voltage Decoupling and bypass caps required	
16	RF out	DC blocked and 50 ohm matched	
9	Vgg	Power supply voltage Decoupling and bypass caps required	

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### Applications Information

#### Application Circuit



#### Biasing and Operation

The CMD245C4 is biased with a positive drain supply and positive gate supply. Performance is optimized when the drain voltage is set to +5.0 V. The recommended gate voltage is +3.0 V.

Turn ON procedure:

1. Apply drain voltage  $V_{dd}$  and set to +5 V
2. Apply gate voltage  $V_{gg}$  and set to +3 V

Turn OFF procedure:

1. Turn off gate voltage  $V_{gg}$
2. Turn off drain voltage  $V_{dd}$

RF power can be applied at any time.

**GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.**

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